

RECEIVED
CENTRAL FAX CENTER

AUG 20 2008

IN THE CLAIMS

Claims 1-10 (Canceled).

11 (Previously Presented). A method comprising:
using 1,2,4,5-tetraaza-3,6-disilacyclohexane as a silicon precursor to form silicon nitride film at a temperature less than 500°C.

Claims 12-18 (Canceled).

19 (Original). The method of claim 11 further including using a nitrogen precursor selected from one of ammonia, a hydrazine or a substituted hydrazine.

20 (Original). The method of claim 19 further including combining said silicon precursor and said nitrogen precursor in a premixed cocktail with an optional solvent.

Claims 21-36 (Canceled).